

SAMTM data sheet SAM-830-10-1ps-x, λ = 830 nm

Laser wavelength $\lambda = 830 \text{ nm}$

High reflection band $\lambda = 810 ... 845 \text{ nm}$

Absorbance $A_0 = 10 \%$ Modulation depth $\Delta R = 6 \%$ Non-saturable loss $A_{ns} = 4 \%$

Saturation fluence $\Phi_{sat} = 110 \,\mu\text{J/cm}^2$

Relaxation time constant $\tau \sim 1 \text{ ps}$

Damage threshold $\Phi = 1.5 \text{ mJ/cm}^2$

Chip area 4.0 mm x 4.0 mm; other dimensions on request

Chip thickness 450 µm

Protection the SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

 \mathbf{x} = 0unmounted \mathbf{x} = 12.7 gglued on a gold plated Cu-cylinder with 12.7 mm \varnothing \mathbf{x} = 25.4 gglued on a gold plated Cu-cylinder with 25.4 mm \varnothing \mathbf{x} = 12.7 ssoldered on a gold plated Cu-cylinder with 12.7 mm \varnothing

x = 25.4 s soldered on a gold plated Cu-cylinder with 25.4 mm Ø
x = 25.0 w soldered on a water cooled Cu-cylinder with 25.0 mm Ø
x = FC mounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance





